

-	20394	gate adj2 insulating	USPAT;	2002/10/29
-	19039	thin adj2 oxide) (ultrathin adj2 oxide	EPO; JPO	16:07
-	1124	(gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon	USPAT;	2002/10/29
-	188199	hydrogen and oxygen	EPO; JPO	16:07
-	227	(hydrogen and oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT;	2002/10/29
-	101606	hydrogen same oxygen	EPO; JPO	16:08
-	122	(hydrogen same oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT;	2002/10/29
-	80371	hydrogen with oxygen	EPO; JPO	16:13
-	88	(hydrogen with oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT;	2002/10/29
-	1	(hydrogen with oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon) and ISSG	EPO; JPO	16:14
-	9	ISSG "in situ steam generation"	USPAT;	2002/10/30
-	8	(ISSG "in situ steam generation") and gate	EPO; JPO	10:11
-	5957	EEPROM and oxide	USPAT;	2002/10/30
-	54	(EEPROM and oxide) and SONOS	EPO; JPO	10:31
-	280	EEPROM and ("form oxide")	USPAT;	2003/04/27
-	0	EEPROM and ("form oxide") near (oxygen adj3 hydrogen)	EPO; JPO	14:47
-	1	("form oxide") near (oxygen adj3 hydrogen)	USPAT;	2003/04/27
-	184	("wet oxidation" or "steam oxidation") and EEPROM	EPO; JPO	14:52
-	16	((("wet oxidation" or "steam oxidation") and EEPROM) and (ultrathin "ultra thin" "ultra-thin"))	USPAT;	2003/04/27
			EPO; JPO	14:53
			USPAT;	2003/04/27
			EPO; JPO	15:00
			USPAT;	2003/04/27
			EPO; JPO	15:01